Roll No. ....

Total Pages: 3

## BT-3/D-18

33083

## DIGITAL ELECTRONICS Paper: CSE-207(N)

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Time: Three Hours] [Maximum Marks: 75]

**Note:** Attempt *five* questions in all, selecting at least *one* question from each unit. All questions carry equal marks.

1. (a) State De-Morgan's Theorem.

3

(b) Discuss BCD adder design procedure.

4

(c) Draw pin configuration of 555 timer IC.

4

(d) Explain memory decoding.

4

## UNIT-I

2. Discuss Quine Mc-Clusky (QMC) method of Minimization. Simplify the following expression using QMC method also verify the results by K map method

$$F = \Sigma_{A,B,C,D} \text{ m } (1,\,4,\,5,\,6,\,12,\,13,\,14) + \Sigma d(0,\,8,\,9,\,11).$$

15

- 3. (a) Write the small note on the following:
  - (i) CMOS characteristics.
  - (ii) Principle of duality.

10

(b) Realize the following logic equation using only NAND gates:

$$AB + CD = AB \cdot CD$$
.

5

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## UNIT-II

4.	(a)	Differentiate between serial adder and parallel adder we the help of full adder block diagram.	ith 10
	(b)	Explain magnitude comparator.	5
5.	Desi	ign a BCD-to-Gray code convertor using	
	(a)	8:1 multiplexer.	
	(b)	Dual 4: 1 multiplexers and some gates.	(
	(c)	NAND gates only.	15
		UNIT-III	
б.	(a)	Explain the operation of twisted ring counter and g its state diagram.	ive 8
	(b)	Explain master slave flip-flop with the help of diagram	am. 7
7.	Wri	ite short notes on the following:	
	(a)	Shift register counter.	
	(b)	Modulo-n counter.	
	(c)	Sequence generator.	15
UNIT-IV			
8.	(a)	What is dynamic RAM? Explain its cell structure.	7
	(b)	Explain the following in brief:	
		(i) EPROM.	
		(ii) EAPROM.	8

9. Write short notes on the following:

- (a) Memory expansion.
- (b) Implementation of PLA using ROM.

(c) FPGA. 15

